

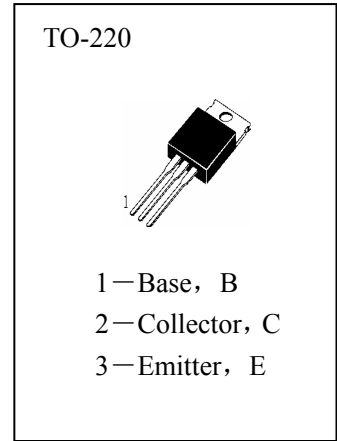


APPLICATIONS

High Voltage Swlitching .

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

- T_{stg}—Storage Temperature..... -55~150°C
- T_j—Junction Temperature..... 150°C
- P_C—Collector Dissipation(Tc=25°C).....60W
- V_{CBO}—Collector-Base Voltage.....400V
- V_{CEO}—Collector-Emitter Voltage.....200V
- V_{EBO}—Emitter-Base Voltage.....6V
- I_C—Collector Current (DC)7A
- I_{CP}—Collector Current(Pulse).....10A
- I_b—Base Current.....4A



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
ICES (1)	Collector Cut-off Current			5	mA	V _{CE} =400V, V _{EB} =0
ICES (2)				100	μ A	V _{CE} =250V, V _{EB} =0
ICES (3)				1	mA	V _{CE} =250V, V _{EB} =0 (Tc=125°C)
IEBO	Emitter Cut-off Current			1	mA	V _{EB} =6V, I _C =0
HFE	DC Current Gain	10				V _{CE} =1V, I _C =5A
V _{CE(sat)}	Collector- Emitter Saturation Voltage			1	V	I _C =5A, I _B =0.8A
V _{BE(on)}	Base-Emitter On Voltage			1.2	V	V _{CE} =5V, I _C =0.8A
f _T	Current Gain-Bandwidth Product	10			MHZ	V _{CE} =10V, I _C =0.5A
t _{OFF}	Turn OFF Time			0.4	μ S	I _C =5A, I _B =0.8A

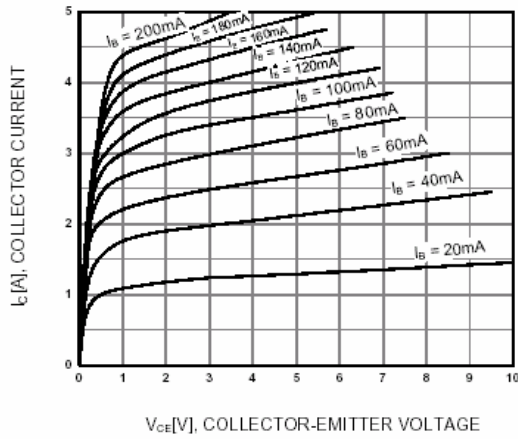
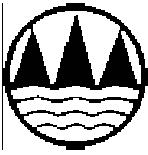


Figure 1. Static Characteristic

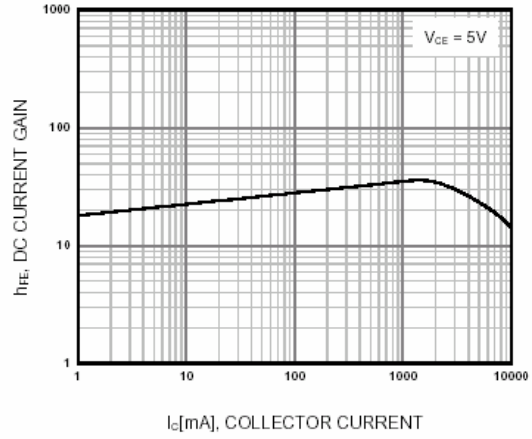


Figure 2. DC current Gain

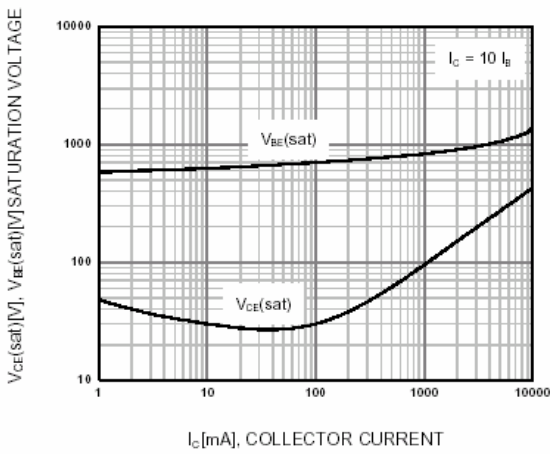


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

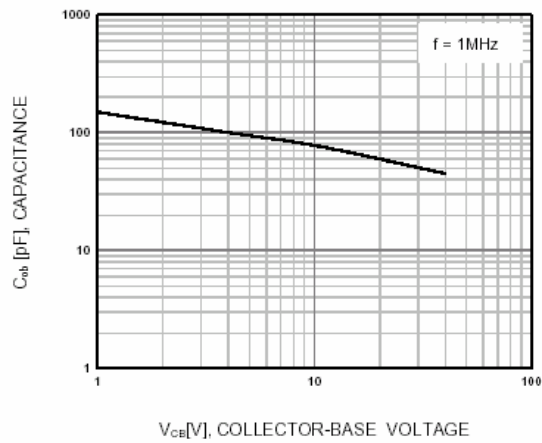


Figure 4. Collector Output Capacitance

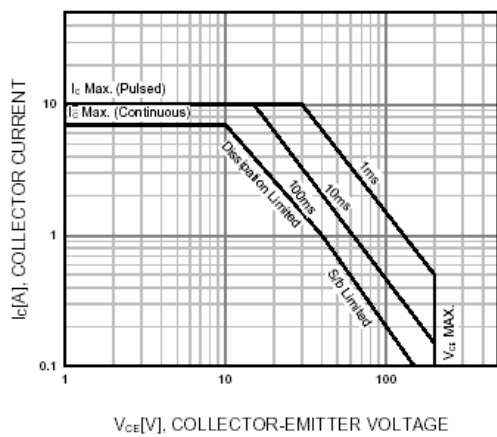


Figure 5. Safe Operating Area

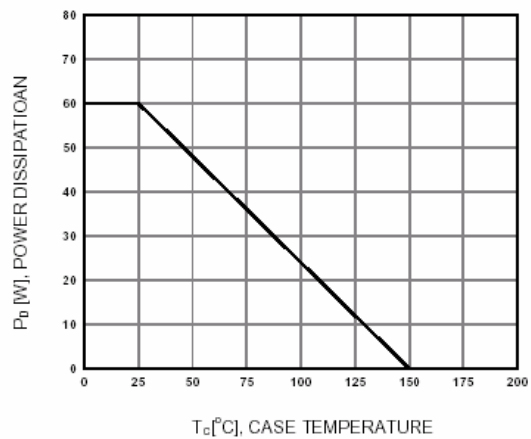


Figure 6. Power Derating